

Isc N-Channel MOSFET Transistor

FDA59N30

• FEATURES

- With To-3P package
- Low input capacitance and gate charge
- Low gate input resistance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

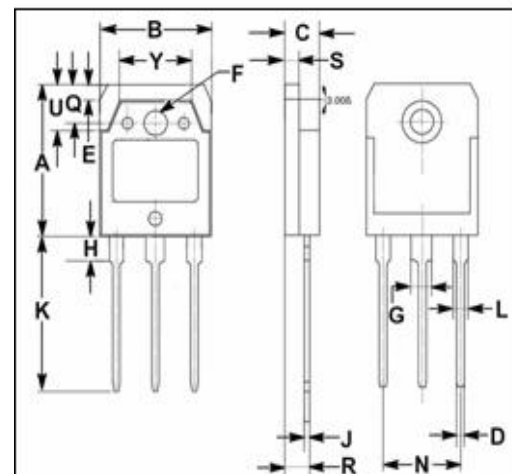
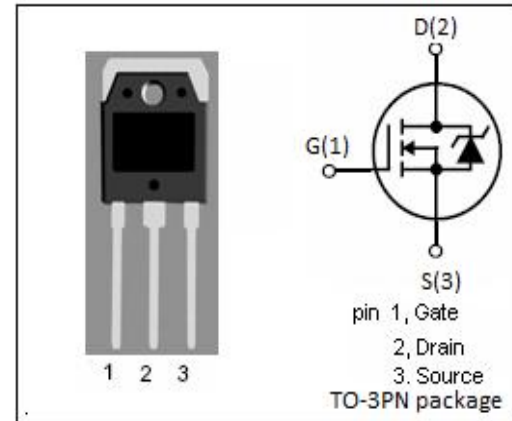
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	300	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous T _c =25°C T _c =100°C	59 35	A
I _{DM}	Drain Current-Single Pulsed	236	A
P _D	Total Dissipation @T _c =25°C	500	W
T _{ch}	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	0.25	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	40	°C/W



DIM	mm	
	MIN	MAX
A	19.60	20.30
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

Isc N-Channel MOSFET Transistor**FDA59N30****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	300			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.25mA$	3.0		5.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=29.5A$		47	56	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=300V; V_{GS}=0V; T_j=25^{\circ}\text{C}$ $V_{DS}=240V; V_{GS}=0V; T_j=125^{\circ}\text{C}$			1 10	μA
V_{SDF}	Diode forward voltage	$I_{SD}=59A, V_{GS}=0V$			1.4	V